

REMARKS

At the outset, the Examiner is thanked for the thorough review and consideration of the pending application. The final Office Action dated May 18, 2007, has been received and its contents carefully reviewed.

Claims 1-4 are withdrawn in this application. Claims 5 and 11 have been amended and no new matter has been added. Claims 1-14 remain pending in this application.

In the Office Action, the disclosure at paragraphs [0020]-[0024] of the specification is objected to because of informalities, and claims 5-14 are rejected under 35 U.S.C. § 112, first paragraph, as failing to comply with the written description requirement and 35 U.S.C. § 112, second paragraph, as failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Applicant respectfully disagrees with the Examiner. However, Applicant has amended paragraphs [0020]-[0024] and claims 5 and 11. Accordingly, these objection and rejections are now believed to be moot in view of the amendments in the specification and claims 5 and 11.

In addition, the Examiner rejected claims 5-14 under 35 U.S.C. § 103(a) as being unpatentable over Im (U.S. Patent No. 6,368,945). Applicant respectfully traverses this rejection

Claim 5 is allowable over the cited references at least in that claim 5 recites a combination of elements including, for example, "...irradiating the laser beam to the amorphous silicon film through the plurality of slits of the mask, thereby melting and crystallizing first portions of a block, wherein the mask defines a block in the amorphous silicon film and wherein the first portions are crystallized by sequential lateral solidification that grows grains along a first direction from interfaces between solid phase amorphous silicon and liquid phase silicon; stepping the mask in the first direction by several micrometers using the mask stage after completing the crystallization for the first portions; irradiating the laser beam to next portions of the block of the amorphous silicon film through the plurality of slits of the mask stepped, wherein the next portions of the block are adjacent to the first portions, and wherein the stepping of the mask in the first direction by the mask stage and the irradiation of the laser beam thereafter are repeated until a lateral grain growth stops in the block by a collision of laterally grown grains, thereby completing the crystallization within the block in the amorphous silicon film; stepping the X-Y stage block by block in the first direction to crystallize another block of the amorphous silicon film after completing the crystallization in the previous block..." Claim 11 is

allowable over the cited references at least in that claim 11 recites a combination of elements including, for example, "...irradiating a laser beam to the amorphous silicon film through a mask having plurality of slits so that first portions of the amorphous silicon film are melted and crystallized, wherein the mask defines a block in the amorphous silicon film and wherein the first portions are crystallized by sequential lateral solidification that grows grains along a first direction from interfaces between solid phase amorphous silicon and liquid phase silicon; stepping the mask in the first direction by several micrometers after completing the crystallization for the first portions; irradiating the laser beam to next portions of the block of the amorphous silicon film through the plurality of slits of the mask stepped, wherein the next portions of the block are adjacent to the first portions, and wherein stepping the mask in the first direction and irradiating the laser beam thereafter are repeated until a lateral grain growth stops in the block by a collision of laterally grown grains, thereby completing the crystallization within the block in the amorphous silicon film; stepping the substrate block by block in the first direction to correspond to a next block of the amorphous silicon film after completing the crystallization in the previous block, the next block having a portion with uncrystallized silicon film..." None of the cited references teaches or suggests at least this feature of the claimed invention. Accordingly, Applicant respectfully submits that claim 5 and its dependent claims 6-10, and claim 11 and its dependent claims 12-14 are allowable over the cited references.

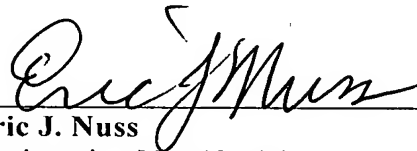
Applicant believes the foregoing amendments place the application in condition for allowance and early, favorable action is respectfully solicited. If for any reason the Examiner finds the application other than in condition for allowance, the Examiner is requested to call the undersigned attorney at (202) 496-7500 to discuss the steps necessary for placing the application in condition for allowance. All correspondence should continue to be sent to the below-listed address.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. § 1.136, and any additional fees required under 37 C.F.R. § 1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911. *A duplicate copy of this sheet is enclosed.*

Respectfully submitted,

Dated: 20 August 2007

By



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